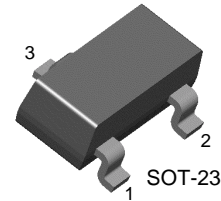


General Purpose Transistor



1. Base 2. Emitter 3. Collector

PNP Epitaxial TY Transistor

Absolute Maximum Ratings $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-600	mA
P_C	Collector Power Dissipation	350	mW
T_{STG}	Storage Temperature	150	$^{\circ}\text{C}$

Electrical Characteristics $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CB0}	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-60		V
BV_{CEO}	* Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}, I_B = 0$	-60		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
I_{CBO}	Collector Cut-off Current	$V_{CB} = -50\text{V}, I_E = 0$		-0.01	μA
h_{FE}	DC Current Gain	$V_{CE} = -10\text{V}, I_C = -0.1\text{mA}$ $V_{CE} = -10\text{V}, I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}, I_C = -10\text{mA}$ * $V_{CE} = -10\text{V}, I_C = -150\text{mA}$ * $V_{CE} = -10\text{V}, I_C = -500\text{mA}$	75 100 100 100 50	300	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.4 -1.6	V V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.3 -2.6	V V
f_T	Current Gain Bandwidth Product	$I_C = -50\text{mA}, V_{CE} = -20\text{V}$ $f = 100\text{MHz}$	200		MHz
C_{ob}	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$		8	pF
t_{ON}	Turn On Time	$V_{CC} = -30\text{V}, I_C = -150\text{mA}$ $I_{B1} = -15\text{mA}$		50	ns
t_{OFF}	Turn Off Time	$V_{CC} = -6\text{V}, I_C = -150\text{mA}$ $I_{B1} = I_{B2} = -15\text{mA}$		110	ns

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Marking

